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The Computer-Derived 1980 Journal Index

The Publication Committee of the Society recommended the use of a computer-derived index in 1968, and this practice is planned to be continued. This index is published two months earlier than the usual index and makes possible indexing more information than before. These indices refer only to *Journal* articles, reviews, brief communications, discussions, and news and reviews listed in the contents pages. They do not include meeting papers, abstracts, and news items. These indices were prepared for the *Journal* by the Institute for Scientific Information® , Philadelphia, Pennsylvania.

Using the Index

1. Given any author, go directly to his name in the author and title index to find the full paper title with a page citation or, if he is a secondary author, to find a cross-reference to a primary author.
2. Given any topic, go to the subject index and search for the key word itself.
3. For a detailed explanation of symbols and abbreviations, see the sample pages before the individual author and title index and the subject index.
4. Chemical formulae cannot be reproduced directly because the conventional computer printout appears in capital letters only. For example, B13 could be three atoms of bismuth or boron triiodide. To avoid this ambiguity, an attempt has been made to write out chemical formulae.
5. In the author index, an author is always listed with all available initials, which for lack of space sometimes can mean omission of one or two letters from the end of his last name. This truncation is indicated by a period at the end of the last name.

The Publication Committee will appreciate comments on the usefulness and accuracy of this index.

PAUL C. MILNER
Chairman
Publication Committee

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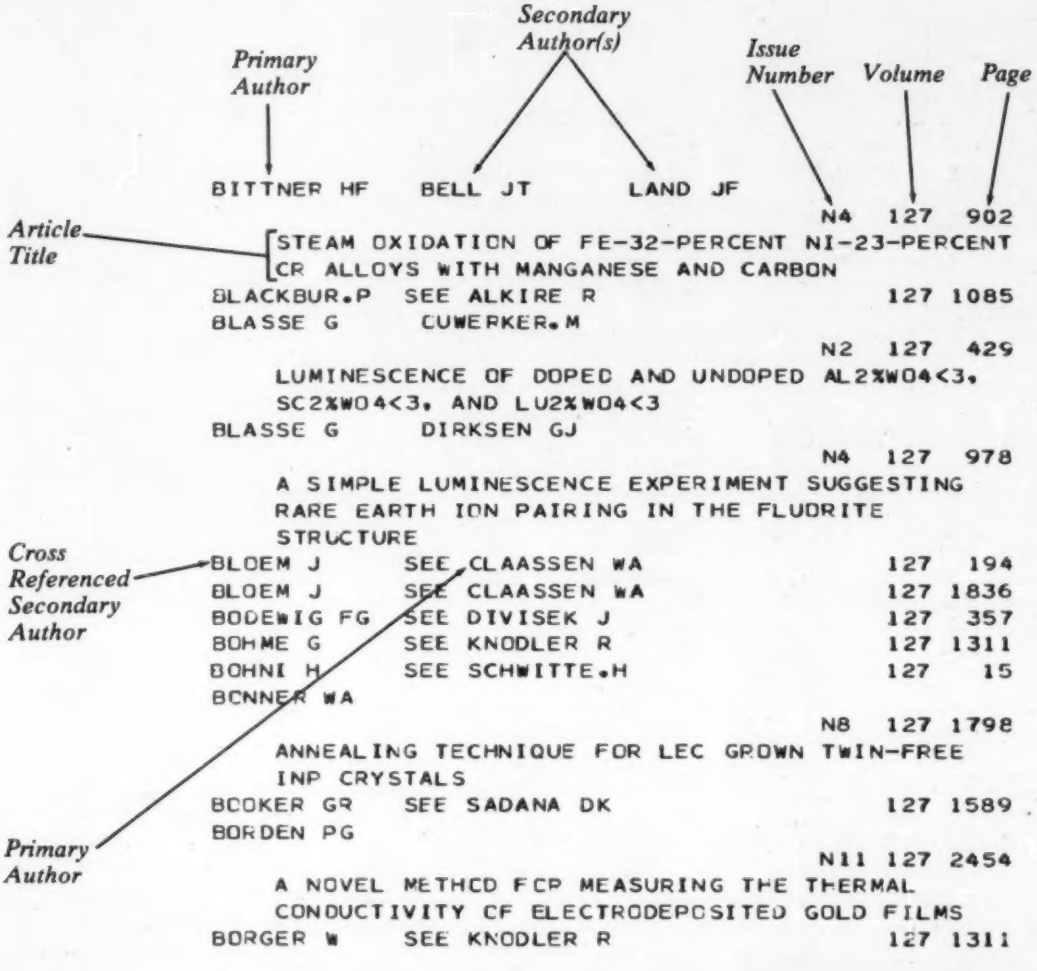
To locate a full description of a source item, look up the primary author. Under a given name, journal articles of primary authorship are described first. Items of secondary authorship follow. These are cross-referenced to the primary author whose name follows the word SEE.



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This word is selected from the contents of one or more articles.

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CURRENT DISTRIBU.	>2017
DENDRITE	8
DIFFUSION	"
ELECTRODE OVERPO.	2017
FAILURE MECHANISM	"
KINETICS	8
MASS TRANSFER	"
POROUS ELECTRODE	2017
POTENTIOSTATIC	1452
PULSE	"
ROUGHNESS	8
TAFEL SLOPE	1452
ZINC CHLORIDE	8
ZINC GROWTH	
DENDRITE	->2335
HYDROGEN EVOLUTI.	"
IMPURITY	"
ROUGHNESS	"
ZINC CHLORIDE	"
ZINC OXIDE	
CVD	->1843
DEPOSITION	->1636
ELECTRICAL PROPE.	"
OPTICAL TRANSMIS.	"
SAPPHIRE	1843
SPUTTERING	1636
THIN FILM	1843
ZINC SELENIDE	
CONDUCTIVITY TYPE	> 983
CVD	->1800
EPITAXIAL GROWTH	"
EPITAXY	-> 937
HETEROEPITAXY	->2295
METALLIC ZINC	"
MOLECULAR BEAM	937
OPEN TUBE METHOD	2295
PHOTOLUMINESCENCE	937
POTENTIAL PROFIL.	983
SCHOTTKY BARRIER	"
VAPOR PHASE TRAN.	1800
VPE	2295
ZINC SULFOSELENI.	1800
ZINC TELLURIDE	937
ZINC SILICATE	
ENERGY TRAP	->2458
PHOSPHOR	"
PHOSPHORESCENCE	"
PHOTOLUMINESCENCE	"
ZINC SULFIDE	
D-A RECOMBINATION	509
ELECTROLUMINESCE.	" >2220
MANGANESE DOPING	"
MEMORY EFFECT	"
RECOMBINATION PR.	509
ZINC SULFOSELENI.	
CVD	->1800
EPITAXIAL GROWTH	"
VAPOR PHASE TRAN.	"
ZINC SELENIDE	"
ZINC TELLURIDE	
EPITAXY	-> 937
MOLECULAR BEAM	"
PHOTOLUMINESCENCE	"
ZINC SELENIDE	"
ZIRCALOY	
CERAMICS	-> 75
HEAT TREATMENT	"
METAL	"
SILICA	"
SILICON	"
VAPOR TRANSPORT	"
ZIRCONIUM	"
ZIRCALOY-2	
FUSED SALTS	->2566
NITRATE	"
NITRITE	"
OXIDATION	"
POLARIZATION	"
ZIRCONIUM	"
ZIRCONIA	
CALCIA STABILIZED	>2325
DEFECT STRUCTURE	"
DIFFUSION	"
GEOTHERMAL BRINE	>2122
IONIC CONDUCTIVI.	2325
OXYGEN ELECTRODE	2122
PH SENSOR	"
YTTRIA STABILIZED	"
ZIRCONIA CELL	
CERMET CATHODE	-> 804
SPUTTERED CERMET	"
WATER ELECTROLYS.	"
ZIRCONIA ELECTRO.	
CERAMICS	->2375
COULOMETRY	"
ION TITRATION	"
MOLTEN SALTS	"
OXIDE	"
ZIRCONIA INTERFA.	
D-C POLARIZATION	>2620
OXYGEN	"
PLATINUM	"
POROUS ELECTRODE	"
SOLID ELECTROLYTE	"
ZIRCONIUM	
ALUMINUM	-> 670
ALUMINUM OXIDE	"
AUGER ELECTRON S.	>2738
CERAMICS	-> 75
CHEMISORPTION	2738
FUSED SALTS	->2566
HEAT TREATMENT	75
IODINE	2738
ISOTHERMAL OXIDA.	670
METAL	75
NICKEL	670
NITRATE	2566
NITRITE	"
OXIDATION	"
POLARIZATION	"
SCALE ADHESION	670
SCALE SPALLING	"
SILICA	75
SILICON	"
STRESS CORROSION	2738
VAPOR TRANSPORT	75
ZIRCALOY	"
ZIRCALOY-2	2566
ZIRCONIUM ALLOY	
FINITE SPECIMEN	->2188
GEOMETRY	"
OXIDATION KINETI.	"
ZONE PROCESS	
LEAD ACID BATTERY	>2104
LEAD DIOXIDE	"
POROUS ELECTRODE	"
POSITIVE PLATE	"